METHOD FOR FORMING A VIA IN A DAMASCENE PROCESS

ABSTRACT OF THE DISCLOSURE

A method for forming a via in a damascene process. In one embodiment, the present method comprises depositing a material into a via formed using a damascene process. More particularly, in one embodiment, the material which is comprised of a substantially conformal material which has an etch selectivity with respect to the substrate into which the via is formed. Furthermore, in this embodiment, the material is deposited along the sidewalls and the base of the via. Next, the present embodiment etches material such that the via is formed having a profile conducive to the adherence of overlying material thereto. In this embodiment, the etching of the material is performed without substantially etching the substrate into which the via is formed. In so doing, the present embodiment creates a via in a damascene process which allows for the formation of a metallized interconnect which is substantially free of voids.

FIGURE 2F

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